

CH IPLINK P-Channel Enhancement Mode Power MOSFET

Description

The LX3401S combines advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltage as low as 2.5V. This device is suitable for use as a load switch or in other general applications.

Features

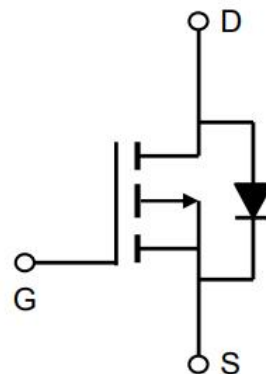
- $V_{DS} = -30V$, $I_D = -4.2A$
 $R_{DS(ON)typ.} = 45m\Omega @ V_{DS} = -10V$
 $R_{DS(ON)typ.} = 51m\Omega @ V_{DS} = -4.5V$
 $R_{DS(ON)typ.} = 65m\Omega @ V_{DS} = -2.5V$
- Low gate charge
- High power and current handing capability
- Termination is Lead-free and RoHS Compliant



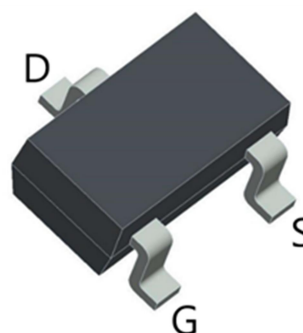
Applications

- PWM Applications
- Load Switch
- Power Management

Schematic Diagram



SOT23 Package



Maximum Ratings

($T_A = 25^\circ C$, unless otherwise noted)

PARAMETER	SYMBOL	MAX	UNIT
Drain-Source Voltage	V_{DS}	-30	V
Gate-Source Voltage	V_{GS}	± 12	V
Continuous Drain Current	I_D	-4.2	A
Pulsed Drain Current ^B	I_{DM}	-20	A
Maximum Power Dissipation ^A	P_D	1.2	W
Junction and Storage Temperature Range	T_J, T_{STG}	-55 to 150	$^\circ C$

Thermal Characteristic

PARAMETER	SYMBOL	MAX	UNIT
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	104	$^{\circ}\text{C/W}$

Electrical Characteristics

($T_A = 25^{\circ}\text{C}$, unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V, I _D =-250μA	-30			V
Gate-Threshold Voltage	V _{th(GS)}	V _{DS} = V _{GS} , I _D =-250μA	-0.7	-0.9	-1.3	V
Gate-body Leakage	I _{GSS}	V _{DS} =0V, V _{GS} =±10V			±100	nA
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =-24V, V _{GS} =0V			-1	μA
Drain-Source On-Resistance	R _{DS(ON)}	V _{GS} =-10V, I _D =-4.2A		45	55	mΩ
		V _{GS} =-4.5V, I _D =-4A		51	68	mΩ
		V _{GS} =-2.5V, I _D =-1A		65	88	mΩ
Forward Transconductance	g _{FS}	V _{DS} =-5V, I _D =-4.2A		10		S
Dynamic Characteristics						
Input Capacitance	C _{iss}	V _{DS} = -15V, V _{GS} =0V, F=1MHz		880		pF
Output Capacitance	C _{oss}			105		
Reverse Transfer Capacitance	C _{rss}			65		
Switching Capacitance						
Turn-on Delay Time	t _{d(on)}	V _{DD} = -15V, I _D =-4.2A V _{GS} = -10V, R _{GEN} =6Ω		7		ns
Turn-on Rise Time	t _r			3		ns
Turn-off Delay Time	t _{d(off)}			30		ns
Turn-off Fall Time	t _f			12		ns
Total Gate Charge	Q _g	V _{DS} = -15V, I _D =-4.2A, V _{GS} =-4.5V		8.5		nC
Gate-Source Charge	Q _{gs}			1.8		nC
Gate-Drain Charge	Q _{gd}			2.7		nC
Drain-Source Diode Characteristics						
Diode Forward Voltage	V _{SD}	V _{GS} =0V, I _D =-4.2A			-1.2	V
Diode Forward Current	I _s				-4.2	A

Notes:

- A. The Power dissipation P_D is based on $T_{J(MAX)}=150^{\circ}\text{C}$, using $\leq 10s$ junction-to-ambient thermal resistance.
- B. Repetitive rating, pulse width limited by junction temperature $T_{J(MAX)}=150^{\circ}\text{C}$. Ratings are based on low frequency and duty cycles to keep initial $T_J=25^{\circ}\text{C}$.
- C. The Static characteristics in Figures are obtained using $<300\mu s$ pulses, duty cycle 2% max.

Typical Electrical and Thermal Characteristics

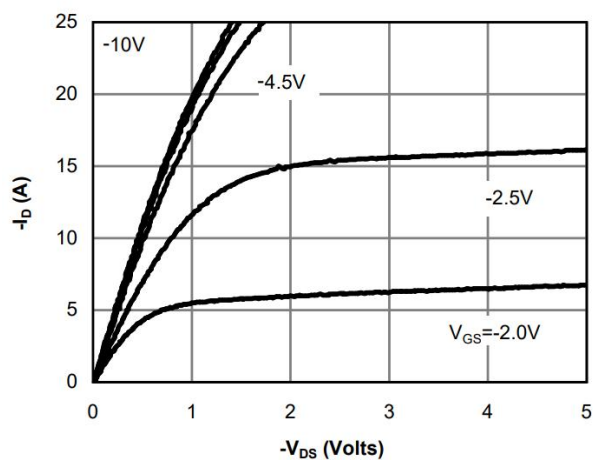


Figure 1. On-region Characteristics

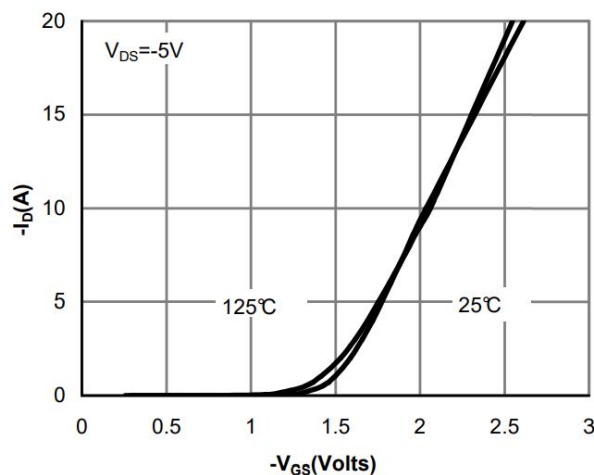


Figure 2. Transfer Characteristics

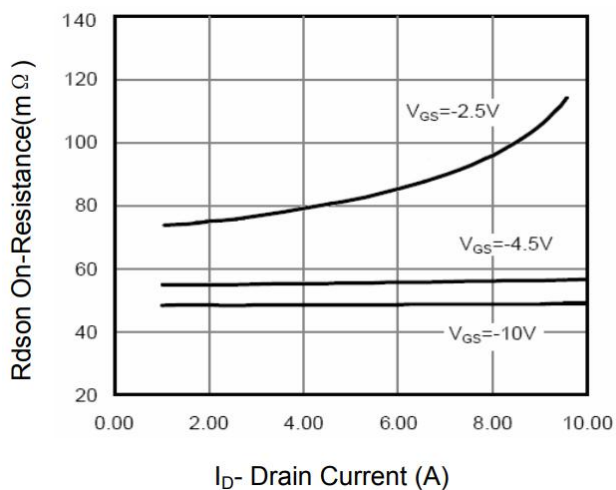


Figure 3. Drain-Source On-Resistance

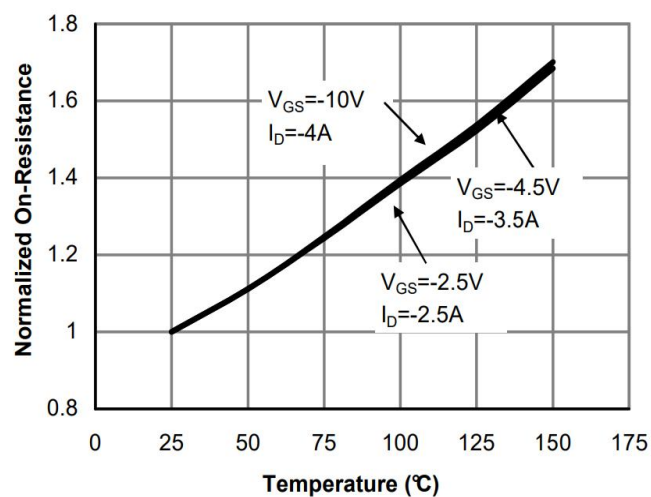


Figure 4. On-Resistance vs. Junction Temperature

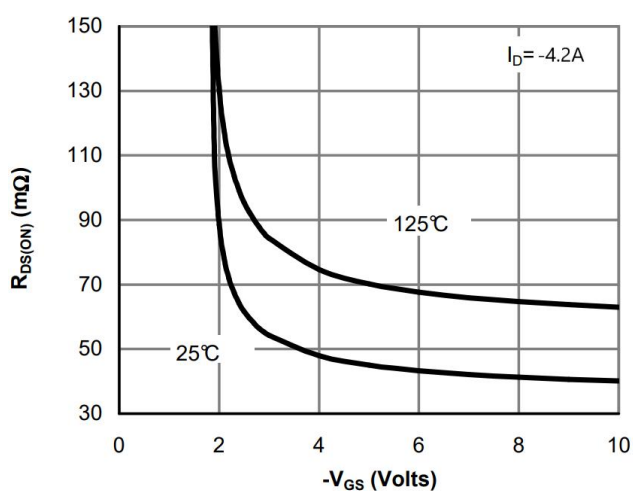


Figure 5. On-Resistance vs. Gate-Source Voltage

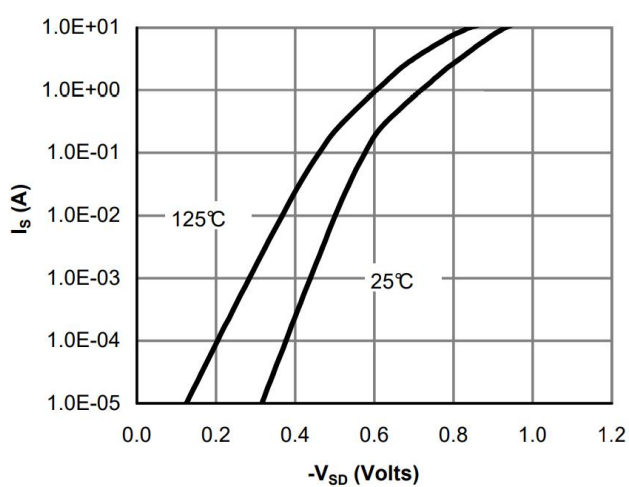


Figure 6. Body-Diode Characteristics

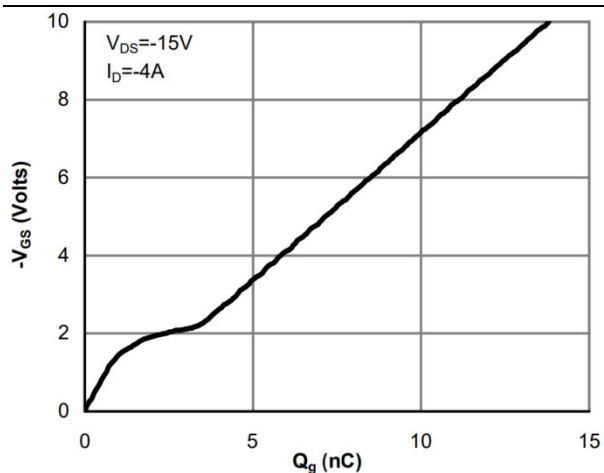


Figure 7. Gate-Charge Characteristics

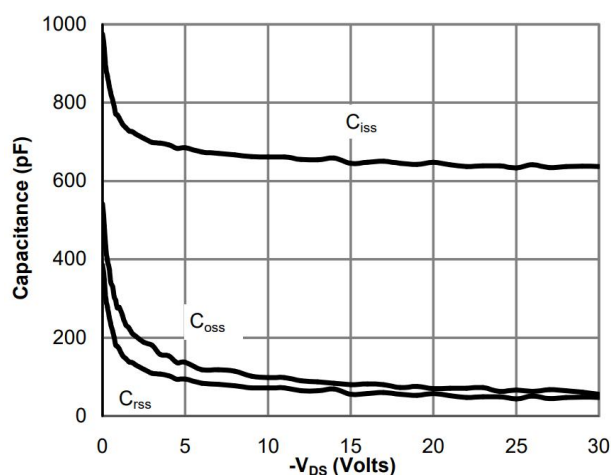


Figure 8. Capacitance Characteristics

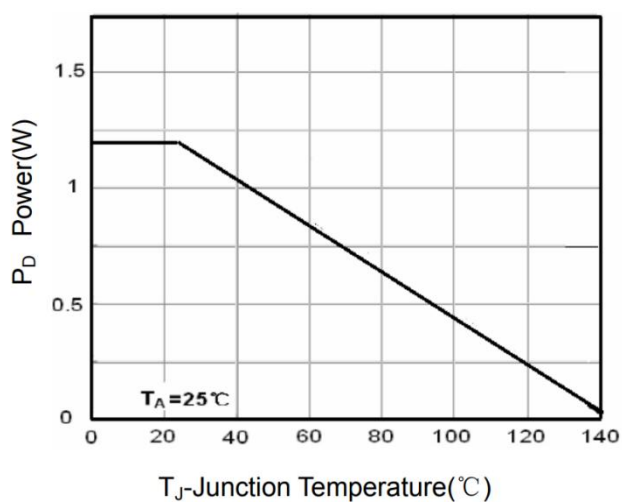


Figure 9. Power Dissipation

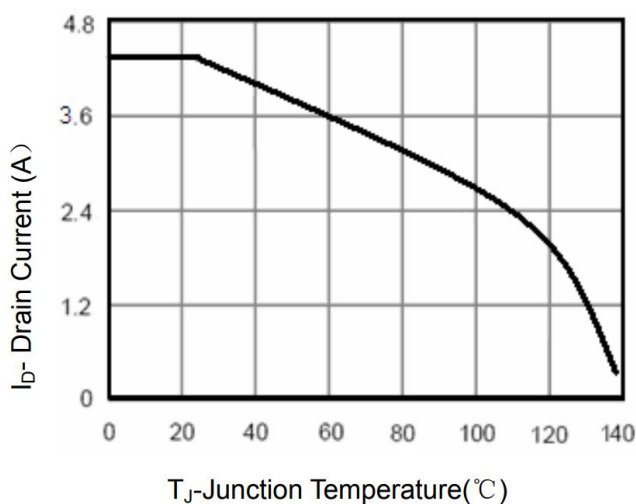


Figure 10. Drain Current

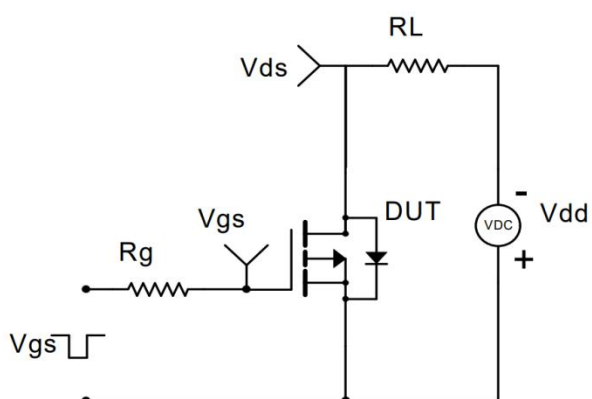


Figure 11. Switching Test Circuit

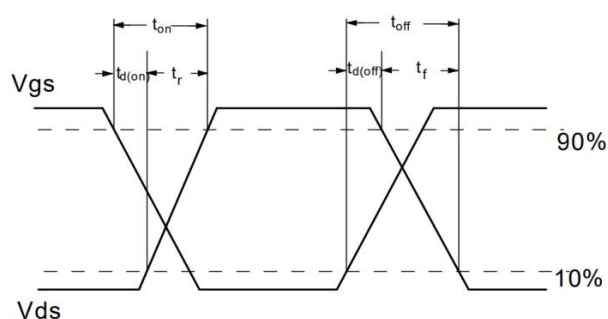


Figure 12. Switching Waveform

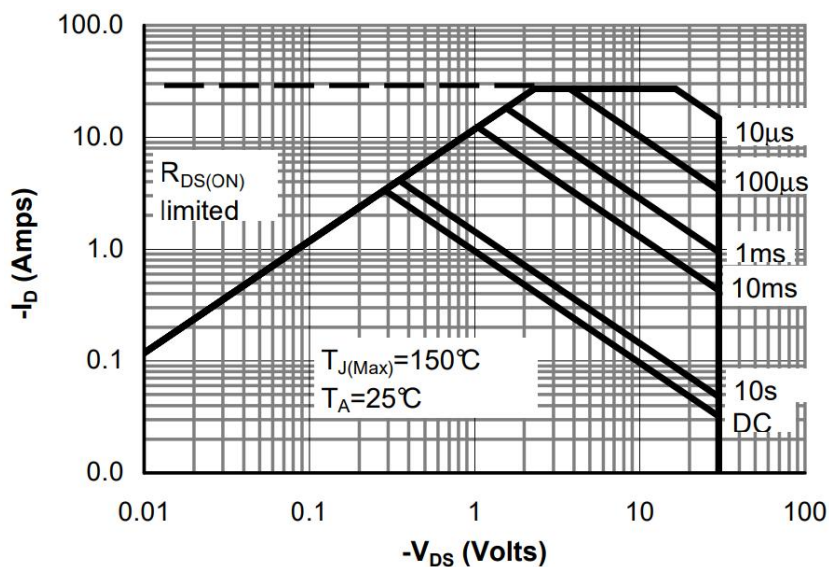


Figure 13. Safe Operation Area

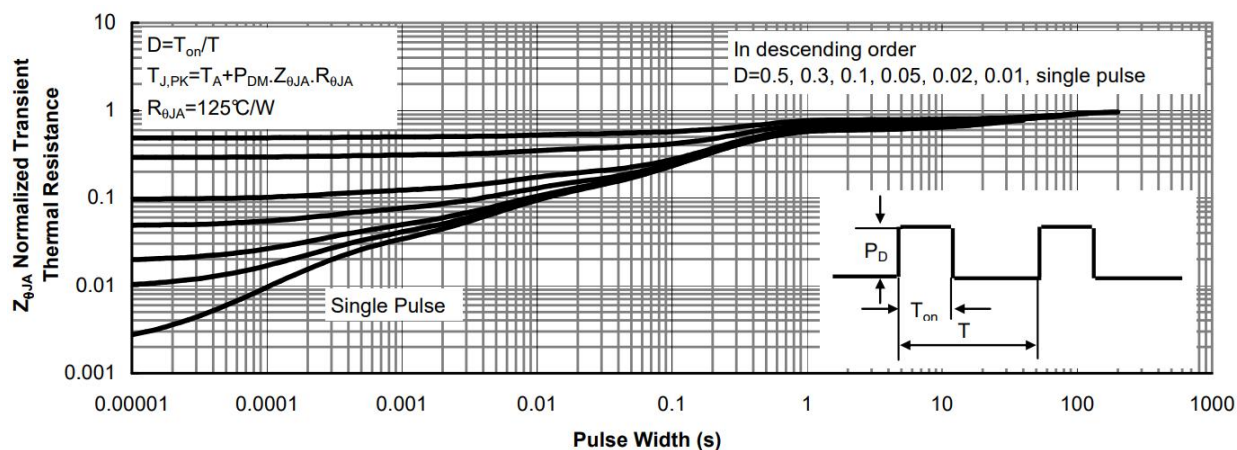
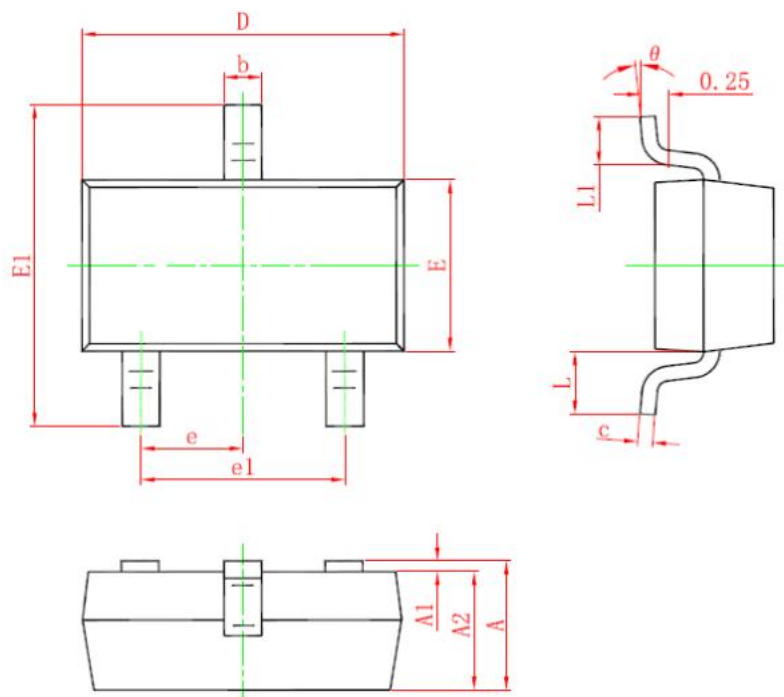


Figure 14. Normalized Maximum transient Thermal Impedance

SOT-23 Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.900	1.150	0.035	0.045
A1	0.000	0.100	0.000	0.004
A2	0.900	1.050	0.035	0.041
b	0.300	0.500	0.012	0.020
c	0.080	0.150	0.003	0.006
D	2.800	3.000	0.110	0.118
E	1.200	1.400	0.047	0.055
E1	2.250	2.550	0.089	0.100
e	0.950 TYP.		0.037 TYP.	
e1	1.800	2.000	0.071	0.079
L	0.550 REF.		0.022 REF.	
L1	0.300	0.500	0.012	0.020
θ	0°	8°	0°	8°

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